

Signal Integrity and Electromagnetic Analyses Techniques for High-speed Interconnects in 3DICs

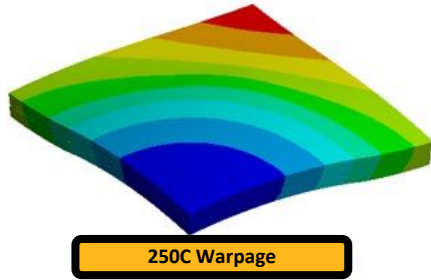
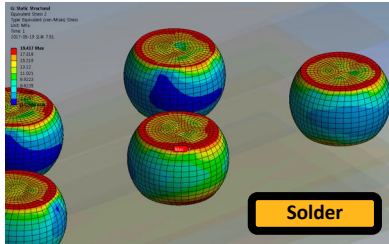
Dr. Yorgos Koutsoyannopoulos

EDPS 2022

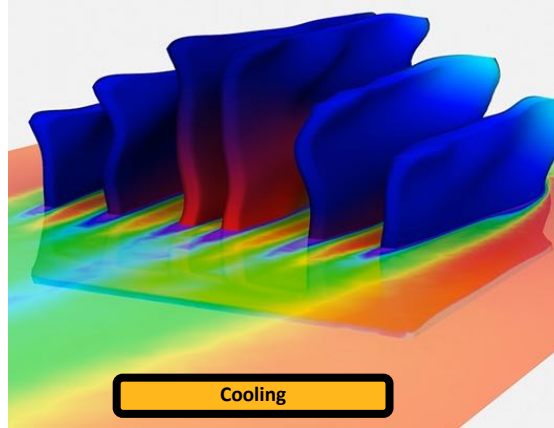


ANSYS Multi-physics Pervasive Simulation

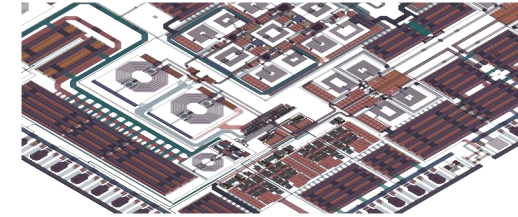
Structural



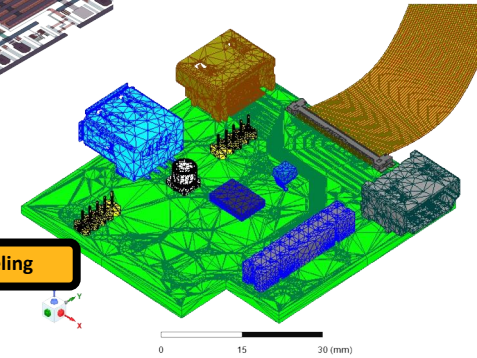
Fluids



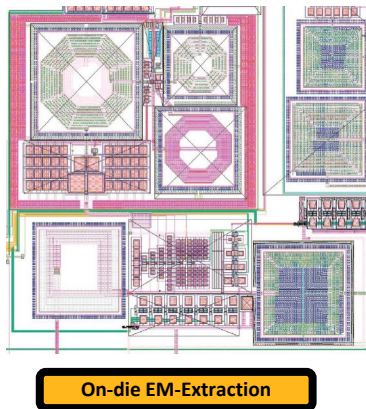
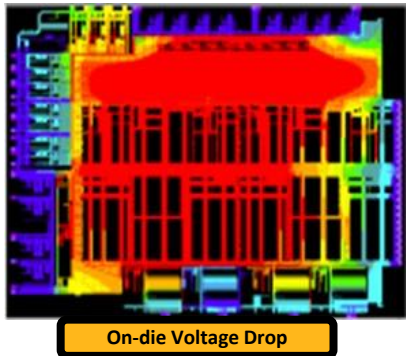
Electronics



Full-Wave Extraction



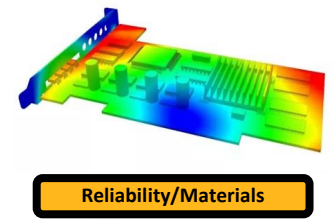
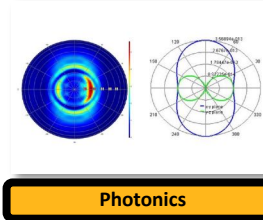
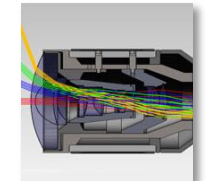
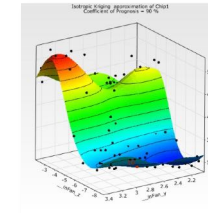
Semiconductors



Cloud

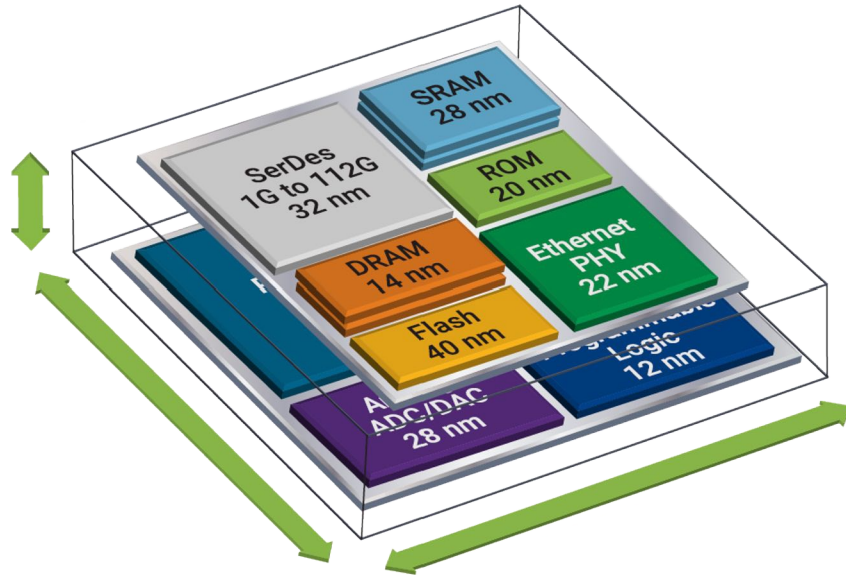


Many Others



3D IC Engineering Challenges

Engineering Goal



Manage effectively **2.5D/3D Heterogeneous Integration** aiming at **maximizing Power-Performance-Area volumic density**

Engineering Requirements

- **Explore** design trade-offs in early stage with physics insights for optimal architecture selection
- **Implement** optimal design with sophisticated helpers (routers, design-rules checkers, ...) and progressive design refinement capabilities
- **Analyze** thoroughly the performance against relevant operating conditions throughout the design process
- **Assess** chip-package to system-level electrical, thermal and structural integrities for reliable, safe and secure, semiconductors solutions
- **Ensure** optimal materials selection for reliability, cost and sustainability targets

/ Delivering Quantified Business Impact

Performance

10%

Higher performance per Watt¹

Speed

30%

Development time reduction²

Cost

50%

Cost reduction³

1) <https://www.ansys.com/advantage-magazine/volume-xiii-issue-2-2019/early-simulation-avoids-chip-burn>

2) <https://www.ansys.com/en-gb/news-center/press-releases/10-23-19-ase-group-significantly-advances-semiconductor-packaging-development>

3) <https://fluidcodes.com/wp-content/uploads/2020/04/crossed-signals-aa-v11-i3.pdf>

/ MULTIDISCIPLINARY COLLABORATION

CO-DESIGN &
CO-ANALYSIS

MATERIALS
INTELLIGENCE

RELIABILITY &
QUALITY

SAFETY &
CYBERSECURITY

/ SILICON TO SYSTEM WORKFLOWS

CHIPLETS
READINESS

HETEROGENEOUS INTEGRATION

DESIGN
EXPLORATION

MULTI-DIE
IMPLEMENTATION

MULTIPHYSICS
ANALYSIS

SYSTEM
VERIFICATION

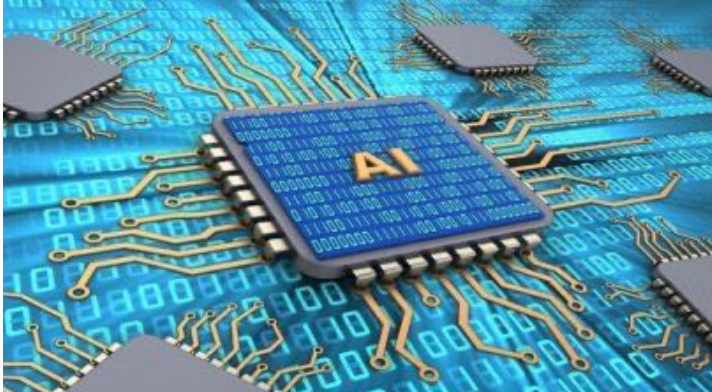


Deep Dive on Solving On-Die Electromagnetic Solutions

Solving the Signal Integrity Problem

Ansys

Target Applications of Electromagnetic Analysis in Auto/5G/6G/QC



AI Processors

SoCs at VERY High Frequencies!

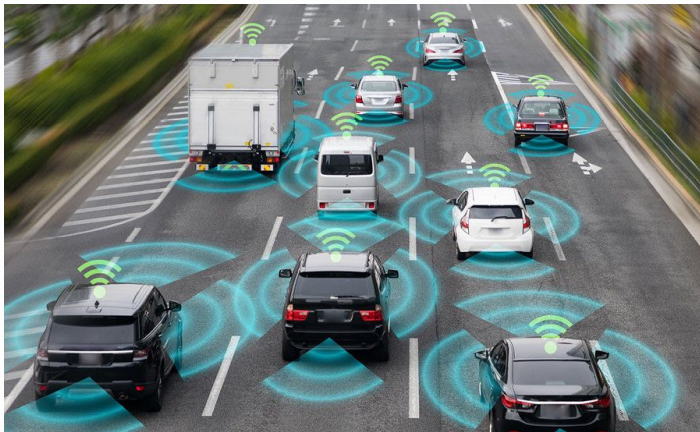
HBM-GPU core multi-Gbps I/O



Superconductive silicon for QC



Cloud Infrastructure
Multi-Gbps networking

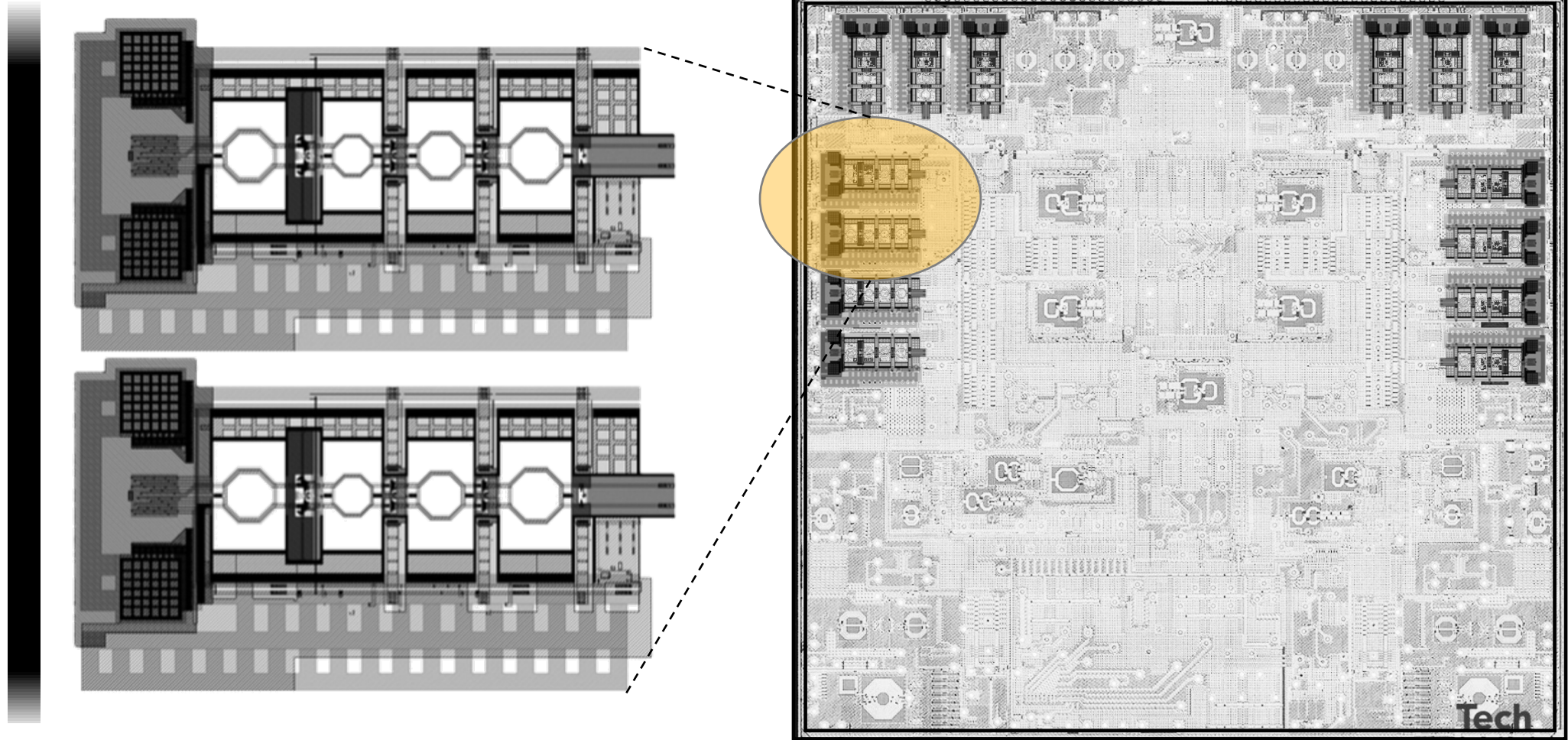


Autonomous Vehicles

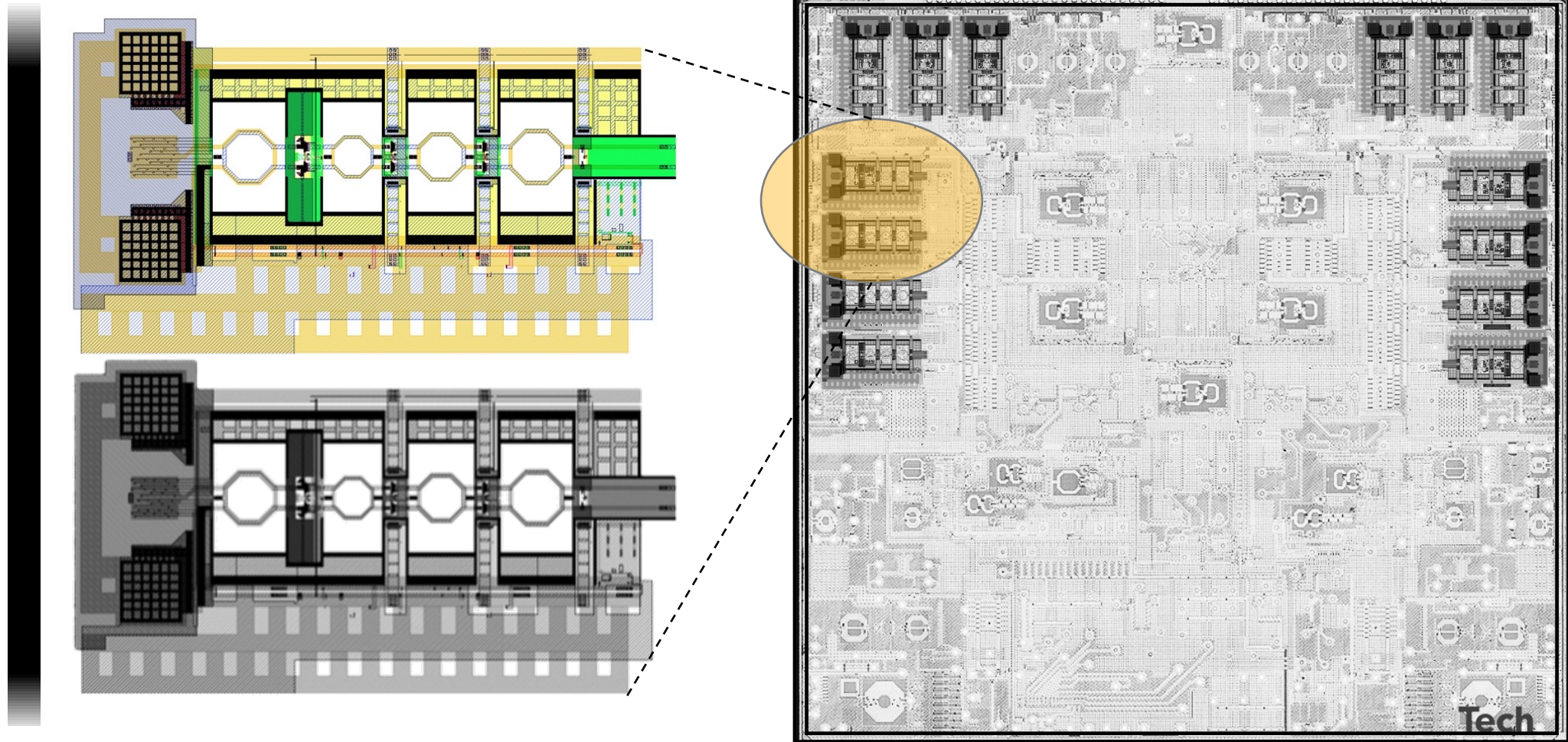


5G/6G Mobile Comms

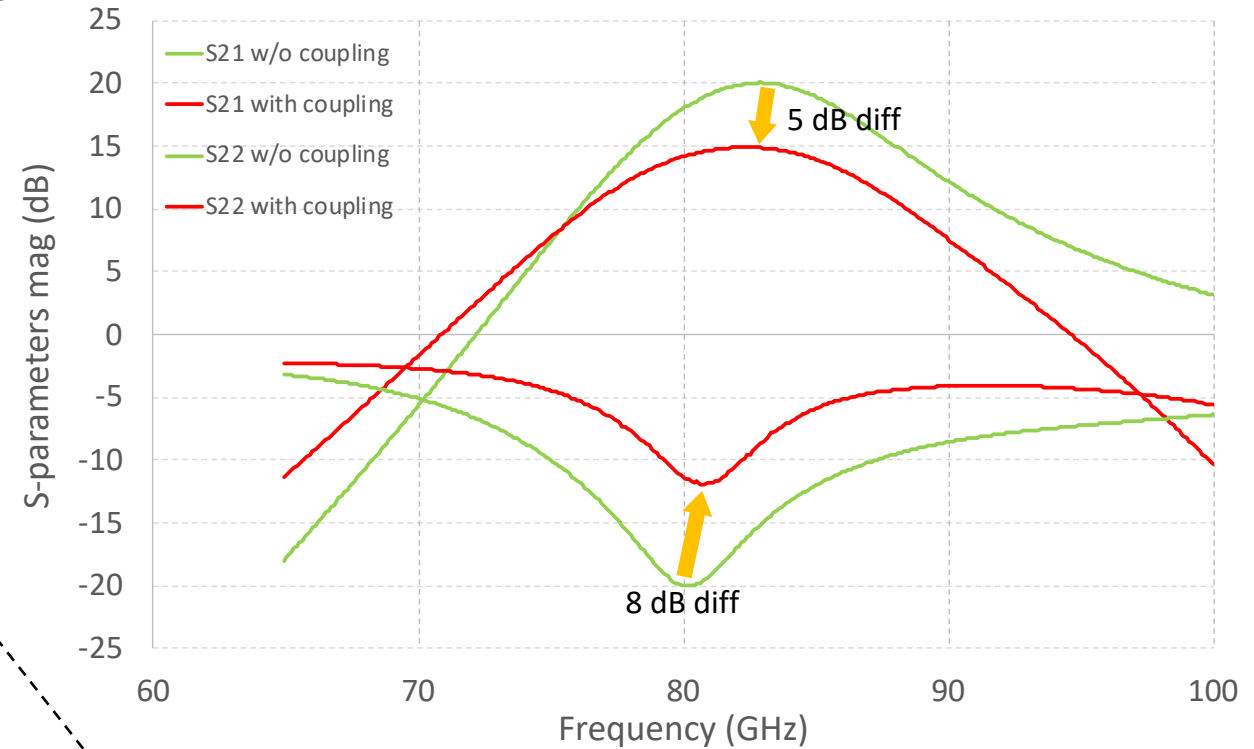
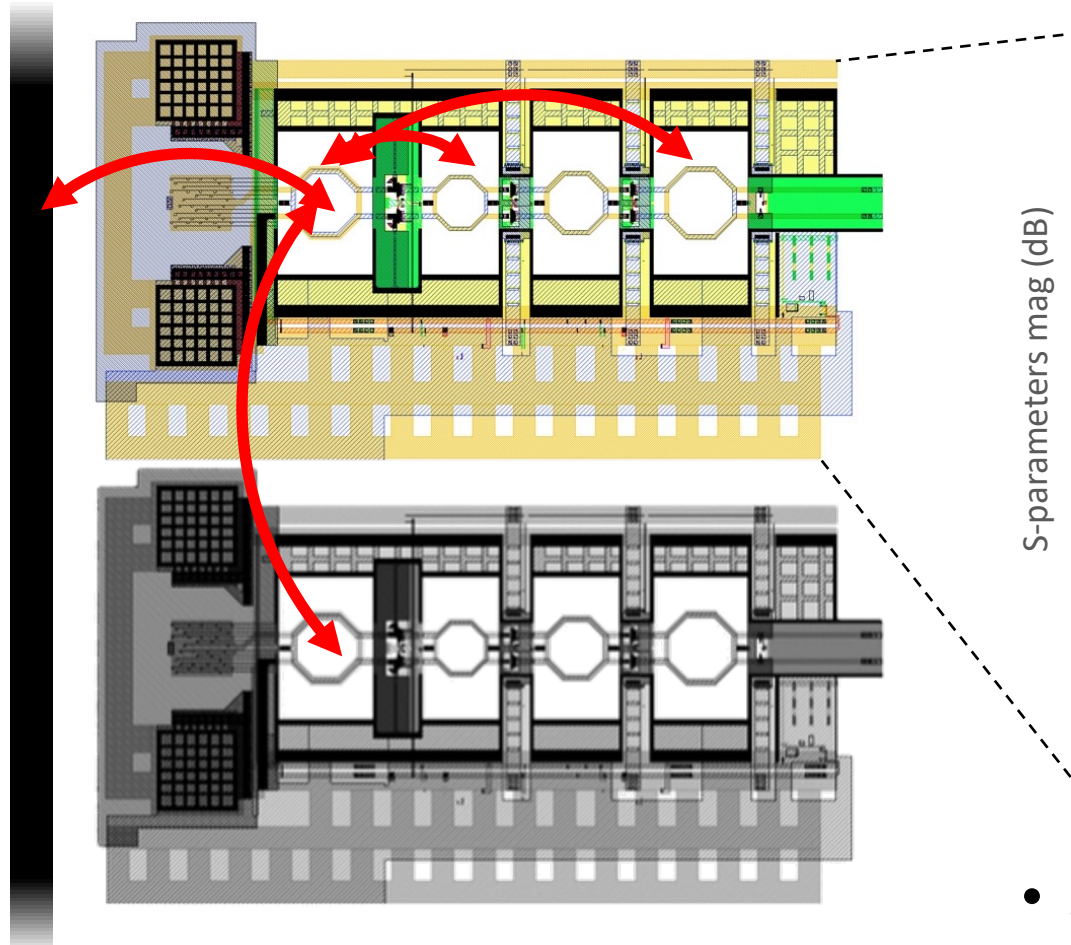
Why EM-aware Matters?



Why EM-aware Matters?



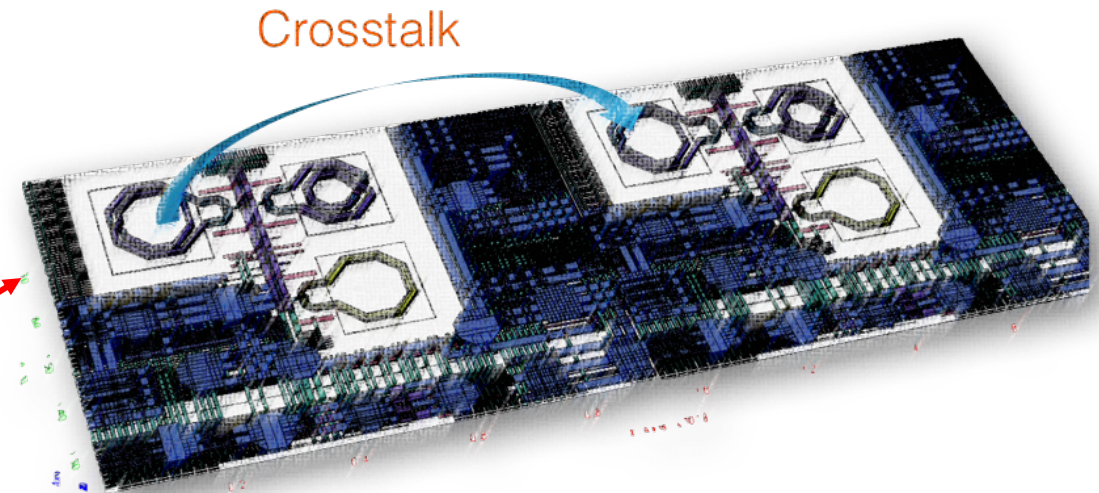
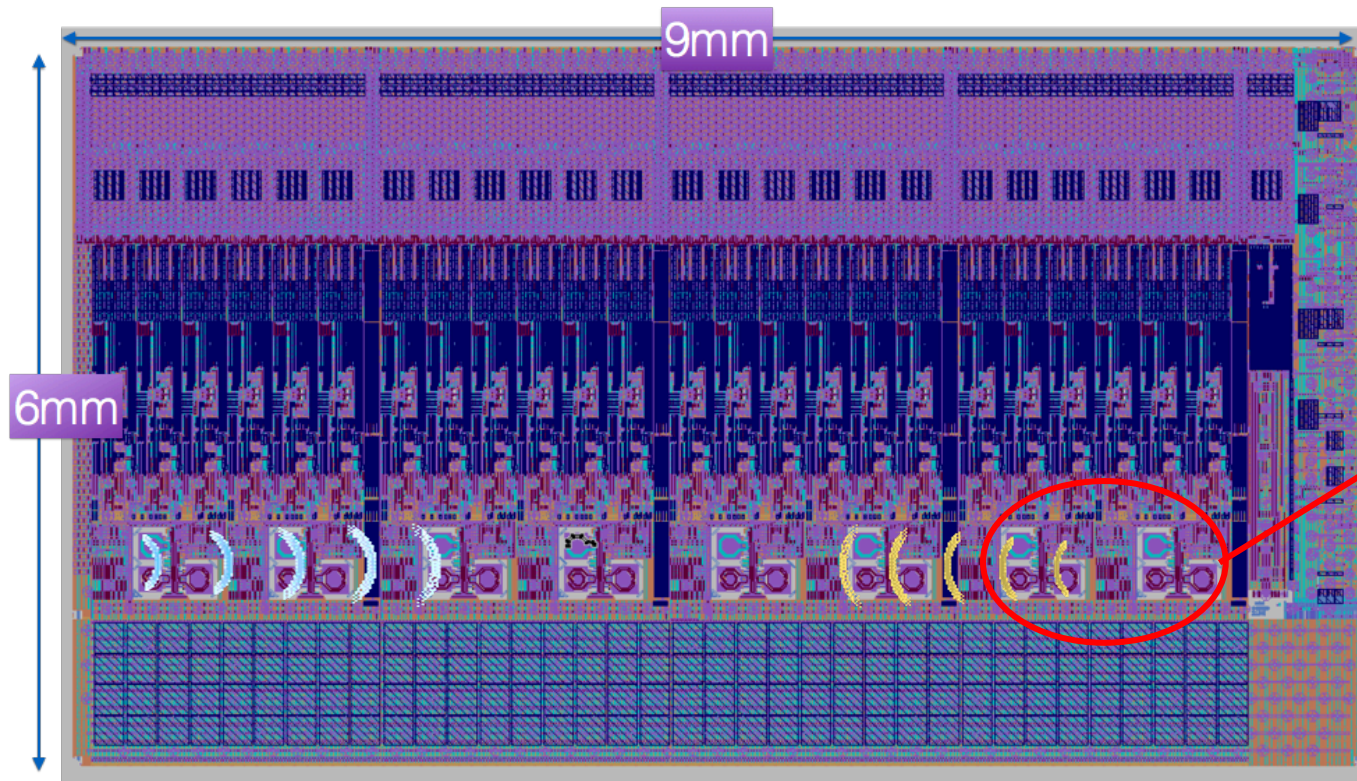
Why EM-aware Matters?



- Significant deterioration of frequency response due to intra-block EM coupling

Mitigating Risks of Electromagnetic Crosstalk at SoC Level

- Ansys provides EM analysis with enough capacity and speed to address large SoC and 3DIC designs up to 3nm CMOS nodes
- Portfolio of products offers complete EM-aware design flow from concept to tape-out sign-off!



A comprehensive EM-aware Workflow for 3DICs and SoCs

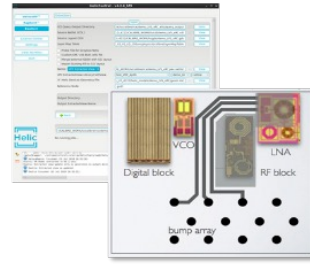
VeloceRF
EMag-Aware Synthesis



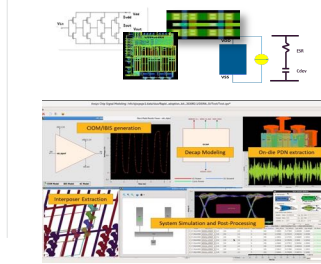
RaptorX/H/Qu
EMag-Extraction



Exalto
Post-LVS EMag Workflow



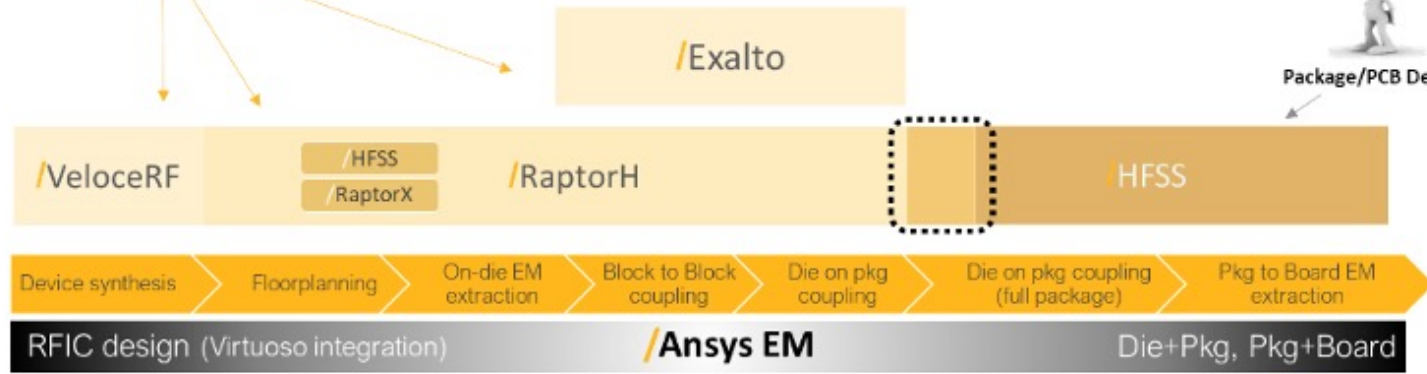
CSM powered by RaptorX
EMag-Aware SI Analysis



RFIC Designer



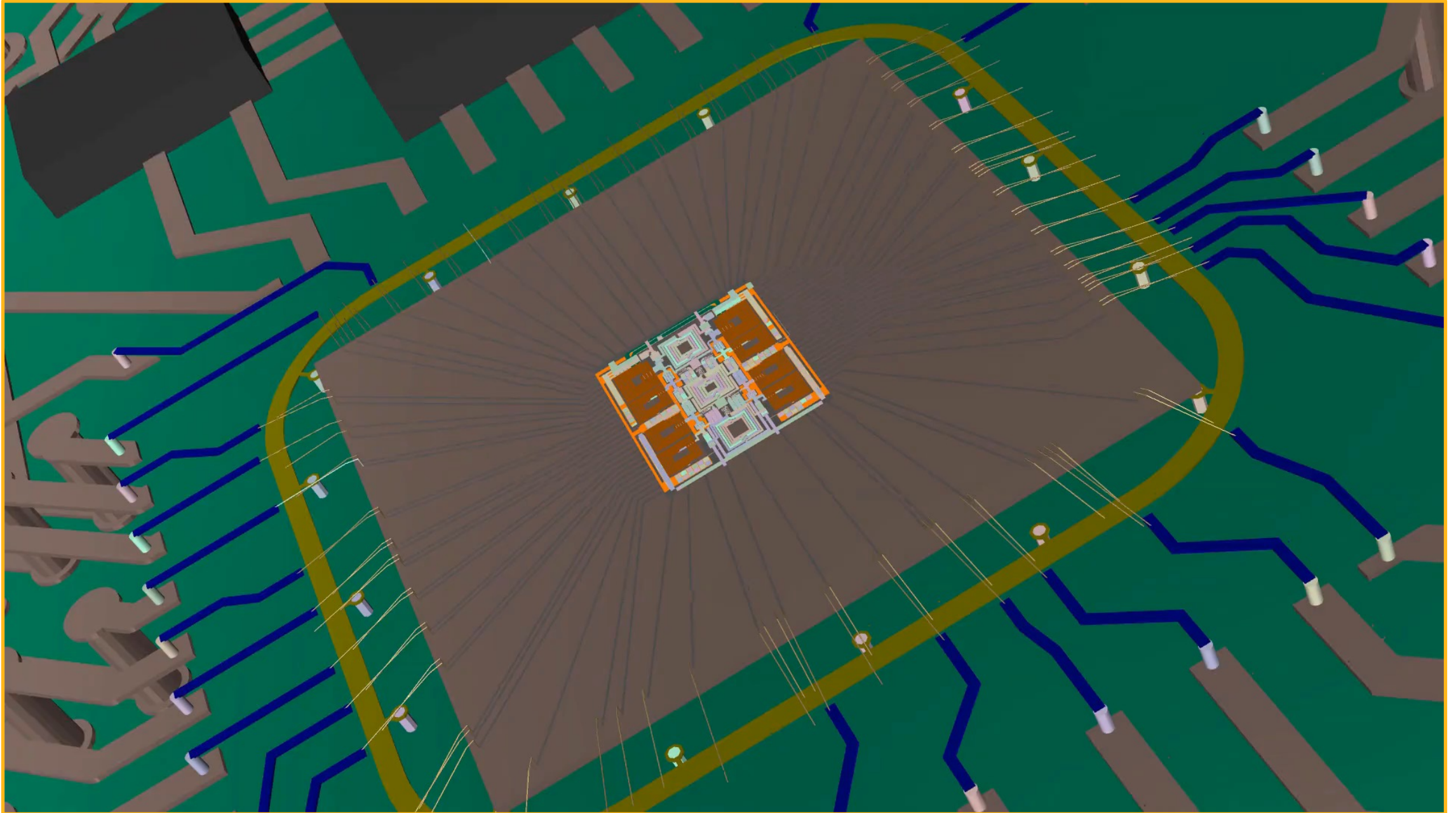
Package/PCB Designer



End-to-End
EM Aware Solutions
& workflows



Simulating Multiscale Problems With HFSS Mesh Fusion



Industry Trends in Electromagnetic Extraction

Advanced Problems in On-Die Electromagnetic
Extraction

Ansys

Who Should Worry About Electromagnetic Extraction?

- Almost all positions:
 - Design managers tasked with system performance
 - Package designers tasked with SI
 - CAD managers tasked with flow development
 - EM experts who advise on advanced EM topics
- Heterogenous design means each party loses some control of your part
 - All parts interact
 - Cannot afford to design in a silo anymore
 - This flow will recapture control of design
- Sign-off on circuit design with SPICE analysis is a given, but must be expanded to full EM sign-off
- Old method of SPICE only sign-off of design, and then performing EM analysis to understand failure once parts are fabricated and tested will no longer work
 - Don't simulate past failure, simulate early for future success
- Two types of 3DIC designers now:
 - Those who care about the problem now
 - Those who will care about the problem for future designs
 - Not if you will care about this, but when

SoCs Trends and EM extraction challenges

Trends

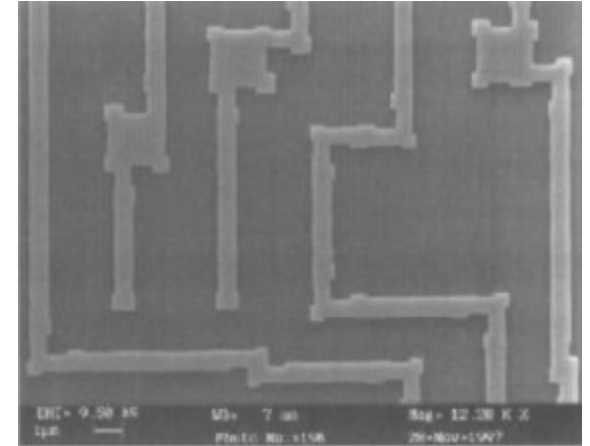
- Frequency escalation – upper 5G frequency bands and sub-THz-range 6G bands
- Rapidly increasing data rates
- Even higher integration and layout density
- Small form factor packaging
 - Extensive use of redistribution layers (RDL)
- 3DIC schemes become mainstream
 - InFO, WoW, CoWoS, iCAP, etc.
- Near-threshold (low-power) design
- Increased need for automatic layout simplification

EM modeling challenges

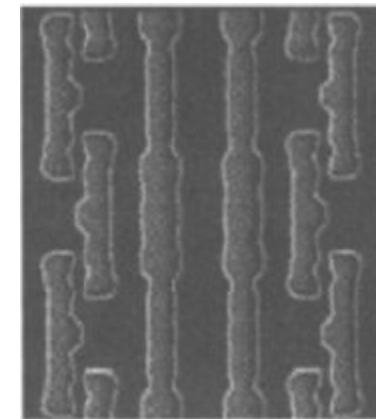
- Increased frequencies entailing higher meshing complexity
- Layout complexity increase
 - Materials
 - Multiple transitions of dielectric layers
 - Density-based definition of electrical and geometrical values
 - Biasing (LDE) effects
 - Millions of via transitions and dummy fill
- Higher integration necessitating co-extraction of
 - Analog and digital
 - Chip and part of package
- EM modeling of structures with hundreds of nets and ports!

Advanced Fabrication Effects

- Also known as “Layout Dependent Effects” (LDE)
- Emerged at 40nm semiconductor processes; effect much more prominent at 28nm and below
- Drawn metal shapes and material parameters become dependent on the actual IC layout density
- What is going to be fabricated is NOT what is drawn in the layout
 - Width, spacing, and resistivity depend on the layout
- Affects conductor dimensions in x, y, z axes as well as material parameters (ϵ_r , R_{sh})
- Effects further exacerbated by multi-patterning
- Relative information provided by means of complex tables integrated in technology files from foundries



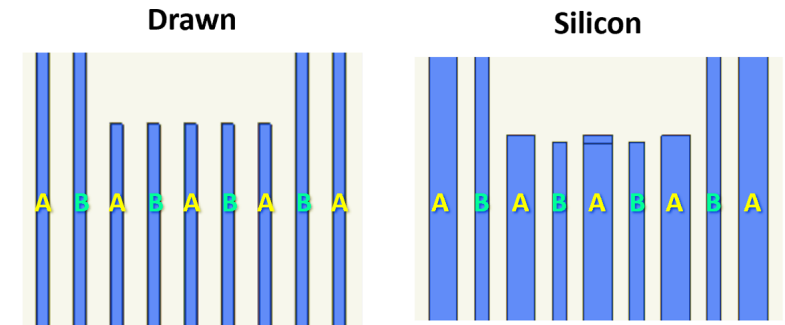
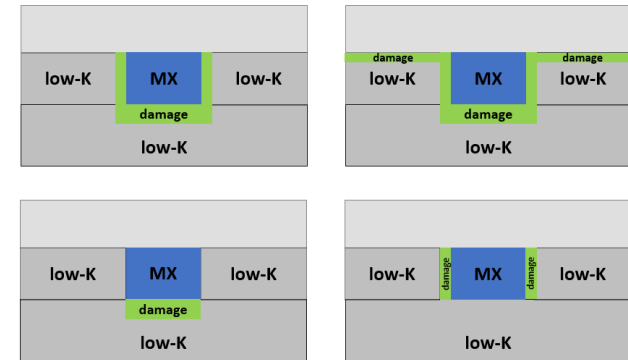
Images: Nanofabrication: Principles, Capabilities and Limits, Zheng Cui, Springer 2010.



Fabrication Effects Considered in Advanced nm Nodes

5, 3 and 2 nm

Category	Description	RaptorX
Conductor	Multi-patterning / Coloring	✓
Conductor	ETCHING (single or multiple tables)	✓
Conductor	Width dependent changes in resistivity over temperature	✓
Conductor	Metal thickness variation (Resistance)	✓
Conductor	Metal thickness and density bounds (Resistance)	✓
Conductor	Metal thickness variation (Capacitance)	✓
Conductor	Metal thickness and density bounds (Capacitance)	✓
Conductor	Sidewall damage thickness variation	✓
Dielectric	Constant damage thickness	✓
Dielectric	Bottom dielectric thickness variation	✓
Dielectric	Side dielectric thickness variation	✓
Via	Via contact resistance varies with via area	✓
Via	Via resistance change over temperature varies with area	✓



Advanced Fabrication Effects Overview

- What is drawn:

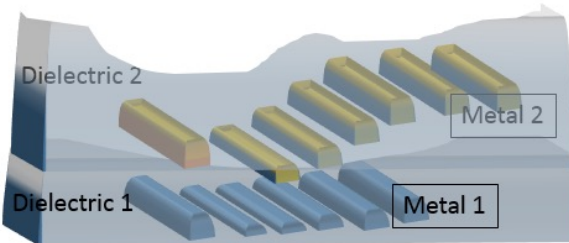
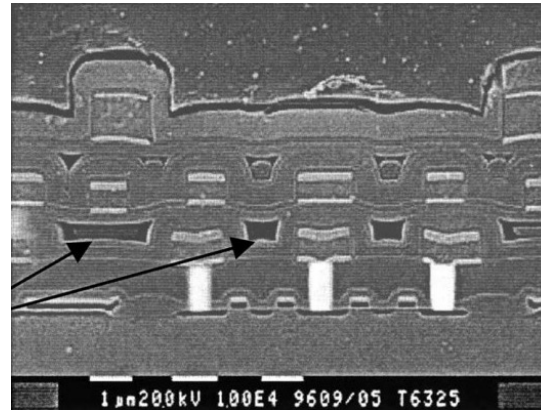
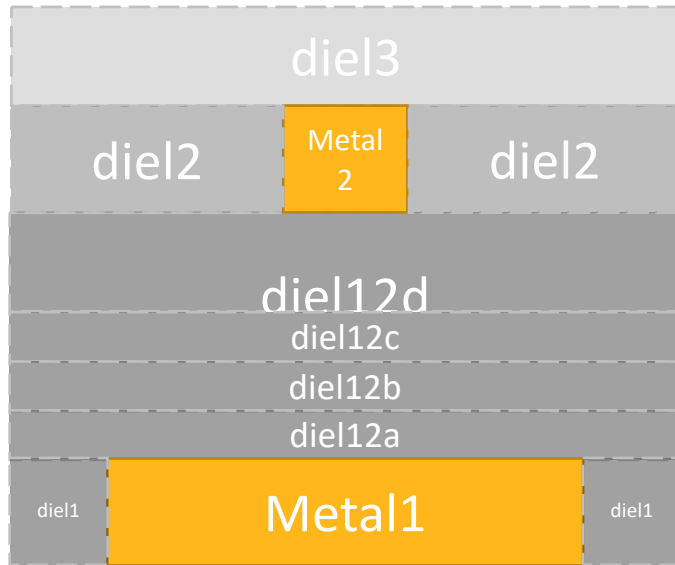
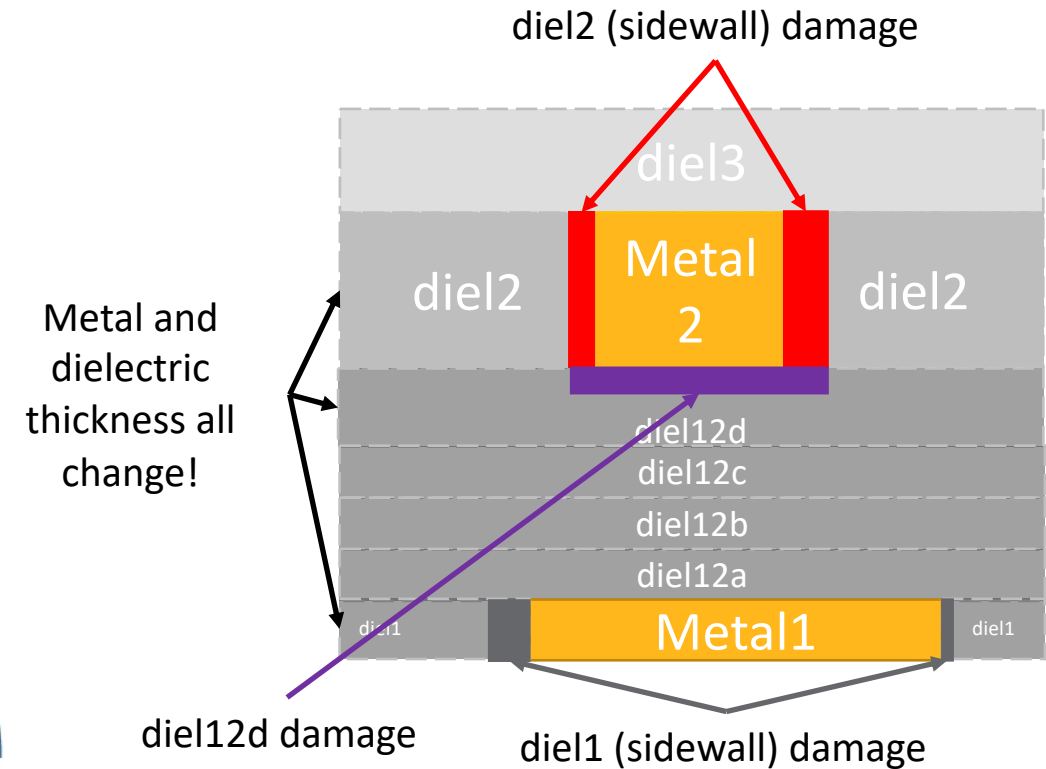


Image source <http://www.vlsi-expert.com/2015/07/importance-of-cmp-process.html>

Nothing is planar, nothing is standard.
Every layout is a different stackup!

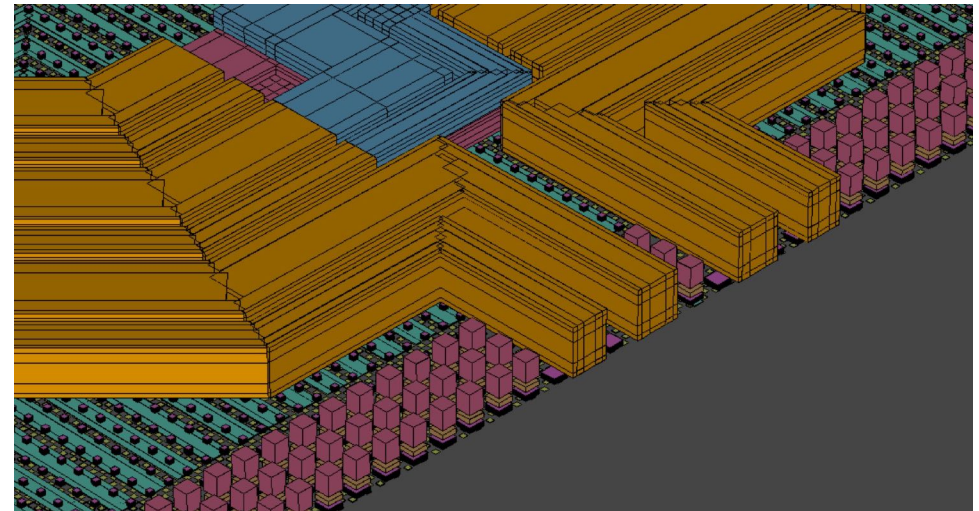
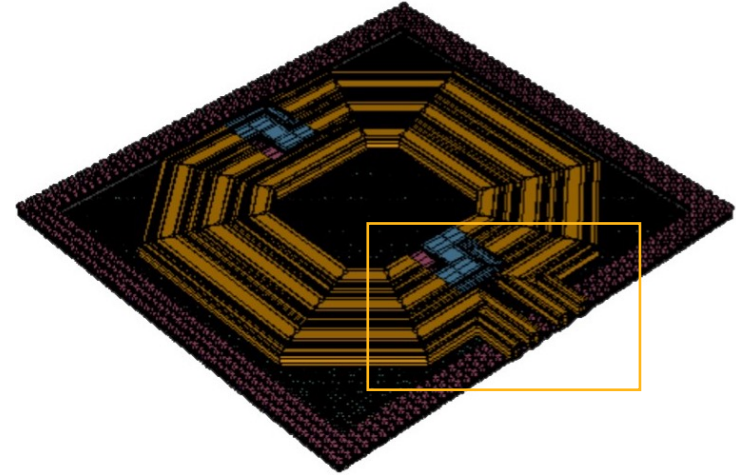
- What is fabricated:



Leads up to 30% difference in resistance
and capacitance!

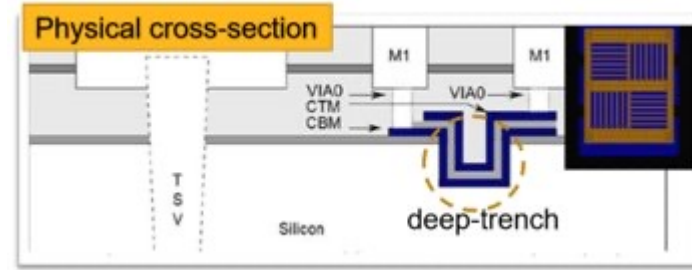
Mechanical Reliability with Metal Dummy Fill

- Unused area must be filled by dense array of "dummy metal tiles"
 - Necessary to ensure functional and reliable chips on each silicon wafer
- Electromagnetic performance is affected by dummy fill but...
- Design complexity explodes
 - Millions of dummy tiles!
 - Even on a device level layout (e.g. spiral inductor)

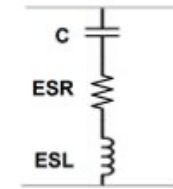


Heterogenous Design w/ Silicon Interposers

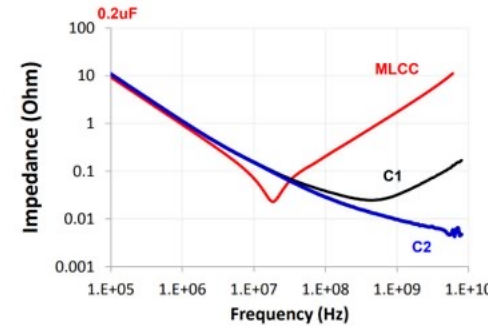
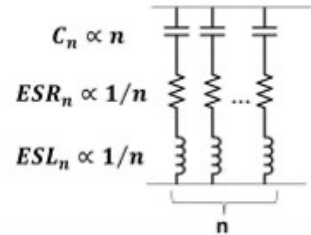
- Heterogenous design allows for process selection and optimization
 - Each part of system can have an optimized process
- Incorporate Ultra high-density capacitors for power integrity
 - Interposer Capacitors (iCAPs)
- Chiplets assembled to form entire system
- Interposer allows for system assembly



Single Capacitor



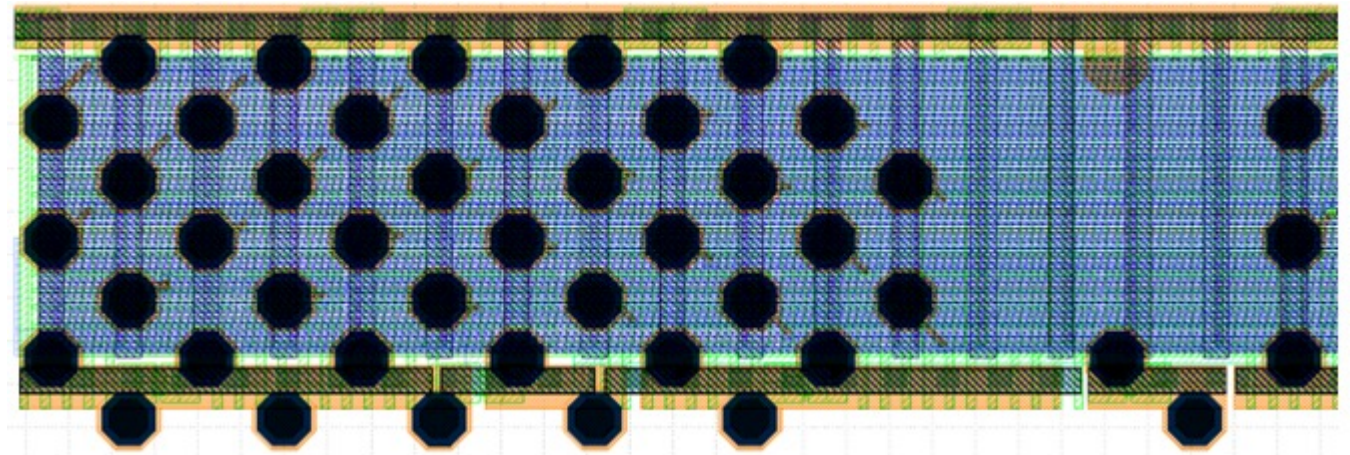
Parallel Capacitors



Surface Mount Capacitor

iCap Design 1

iCap Design 2

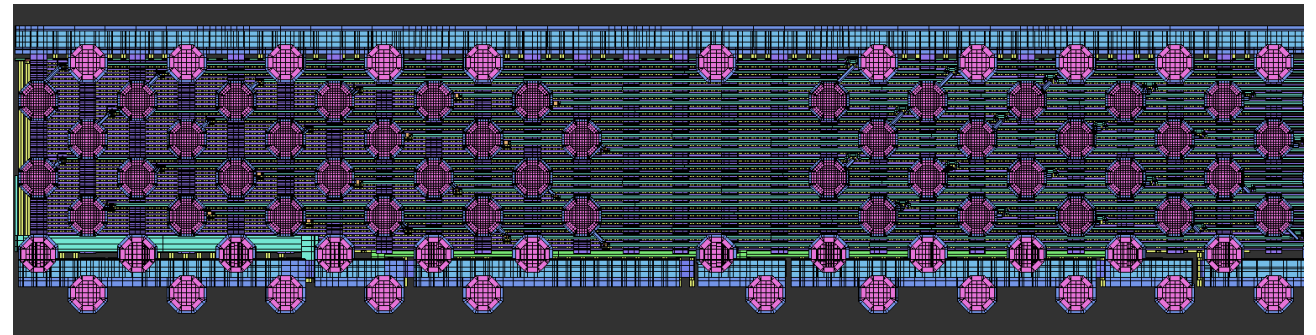


Interposer Example

- Layout used is a ~5mm lane of HBM I/O with 48 signal and VSS/VDD nets
- No manual layout work required to simplify the design
- Layout preprocessing automatically applied by RaptorX or RaptorH
- Size is ~0.3mm x 5mm

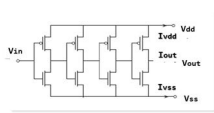
11 signals	RaptorX
Extraction time	5h 40m
Peak memory	170 GB
CPUs	16

48 signals	RaptorX
Extraction time	15h 2m
Peak memory	262 GB
CPUs	16

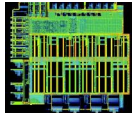


CSM System Signal Integrity Analysis Flow

IO Circuit



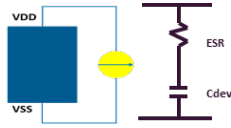
Chip



Interposer



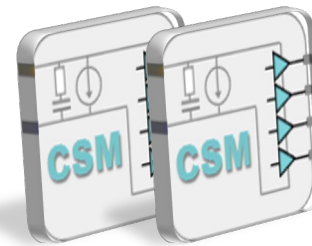
On-die Decap Circuit



CSM Chip Modeling Flow for SI analysis
Powered by RaptorX

The screenshot displays the Ansys Chip Signal Modeling software interface with several key components highlighted:

- CIOM/IBIS generation:** Shows a circuit model and a waveform plot.
- Decap Modeling:** Shows a circuit model with a decoupling capacitor and a waveform plot.
- On-die PDN extraction:** Shows a 3D model of the power distribution network on the die.
- Interposer Extraction:** Shows a 3D model of the interposer structure.
- System Simulation and Post-Processing:** Shows a system-level simulation and a post-processed waveform plot.



Deliver CSM model as a chip model in PKG/PCB system SI analysis

SIwave/AEDT

The screenshot shows the SIwave/AEDT software interface with a 3D model of a chip and a signal integrity analysis plot. The plot displays a complex signal waveform with multiple peaks and troughs, indicating a detailed analysis of the signal integrity.



Conclusion

- Heterogenous designs requires multidisciplinary approach to design to squeeze out the best performance possible
- Signal and power nets must be analyzed together in single EM simulation
- Many issues must be addressed for advanced silicon node sizes
 - Advanced Fabrication Effects
 - Interposer
- Need a way to analyze the different parts of the heterogenous design together
- A comprehensive and fast solution is needed for all these challenges

 **Ansys**

